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Application Note

AN-SMPS-ICE2xXXX-1

CoolSET[™]

ICE2xXXX for OFF – Line Switch Mode Power Supply (SMPS)

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Power Management & Supply



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Operating Principles

The ICE2AXXX is designed for a current-mode flyback configuration in **discontinous (DCM) or** continous conduction (CCM) mode.

The control circuit has a fixed frequency. The duty cycle (D) of the integrated CoolMOS Transistor is controlled to maintain a constant output voltage (V_{OUT}).

Fig. 1 shows the input voltage ($V_{DC IN}$), the primary current(I_{LPK}), and the secondary (I_{SEC}) transformer currentof the flyback converter depicted on p. 3

When the CoolMOS Transistor is swiched on, the initial state of all windings on the transformer is at positive potential.

The rectifier diode (D1) on the secondary side is reverse biased and therefore does not conduct. Consequently no current flows in the secondary winding. During this phase, energy is stored in the inductance of the primary winding and the transformer can be treated as a simple series inductor. Fig. 1 shows that there is a linear increase of the primary current (I_{PRI}) while the CoolMOS Transistor is on.

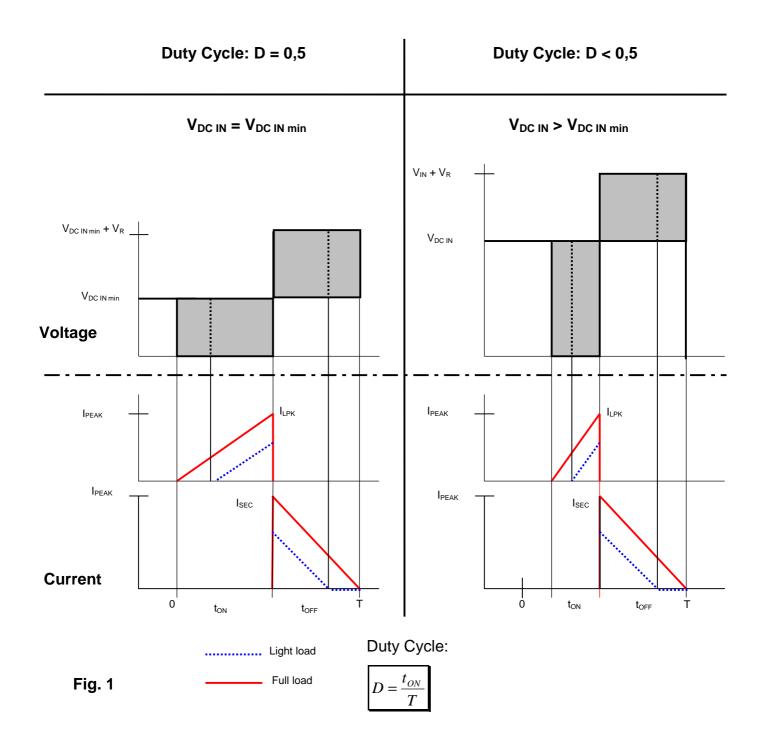
When the CoolMOS Transistor is swiched off, the voltage reverses on all transformer windings (flyback action) until it is clamped by rectifier diode on the secondary side. Now the secondary rectifier diode (D1) is conducting, and the magnetizing energy stored in the transformer core is transferred to the secondary side during the reset interval.

In the **discontinous conduction mode DCM** the secondary current (I_{SEC}) decreases from its peak value to zero (Fig. 1). During this period the whole energy stored in the primary inductance is transferred to the secondary side (neglecting losses and energy stored in the primary leakage inductance), then the next storage cycle starts. Taking into account the transformer turns ratio, the secondary voltage (V_{SEC}) is "reflected" back (V_R) to the primary winding and adds to the input voltage ($V_{DC IN} + V_R$). An additional transient voltage may appear on the primary winding due to energy stored in the uncoupled "leakage" inductance in the primary winding. This voltage is not clamped by the secondary side winding. If the flyback current (I_{LPK} and I_{SEC}) does not reach zero before the next "on" – cycle the converter is operating in **continous conduction mode** (Fig. 2). Note:

When the system shifts to continous conduction operation, its transfer function is changed to a two pole system with low output impedance. In this case additional design rules have to be taken into account including different loop compensation and slope compensation on the primary side.



Voltage and current waveforms in **discontinous conduction mode** (DCM) operation:





Comparison of **continuus conduction** (CCM) and **discontinuus conduction** (DCM) mode.

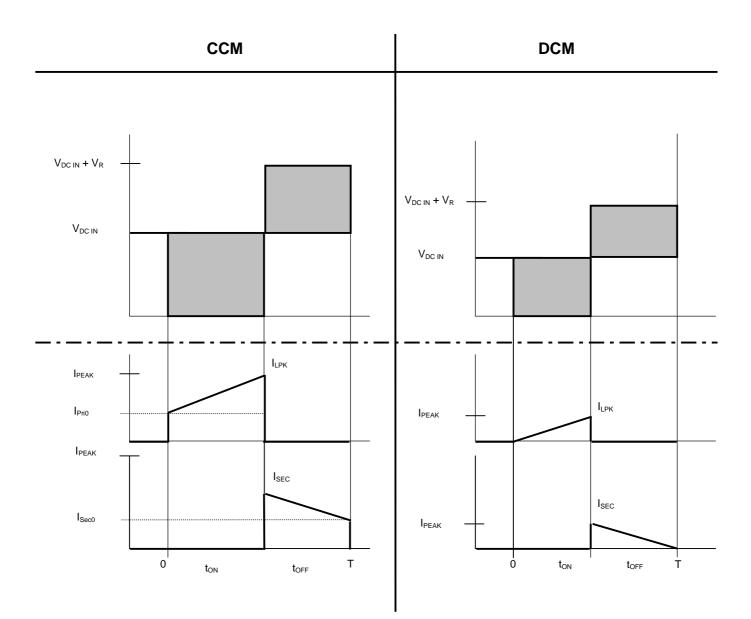


Fig. 2



Input stage

As shown in Fig. 3 the AC input power is rectified and filtered by the bridge rectifier (BR1) and the bulk capacitor C3. This create a DC high voltage bus which is connected to the primary winding of the transformer (TR1). The transformer is driven by the CoolSET integrated high voltage, avalanche rugged CoolMOS transistor, with an external sense resistor (R17) for precision current mesurement.

Output stage

The secondary winding power is rectified and filtered by a diode (D1), capacitors (C5, C9 and C20). The output LC-filter (L3, C23) reduces the output voltage ripple.

Other output voltages

Other output voltages can be realized by adjusting the transformer turn ratio and the output stage.

Chip supply

The current in the bias winding is rectified and filtered by a diode (D2) and a resistor (R8) in order to charge the the supply capacitor (C4). This creates a bias voltage that powers the CoolSET ICE 2AXXX. The resistors R6 and R7 charge the VCC Cap and supply the chip during startup. The Zener diode (D4) clamps the chip supply voltage (Vcc) in order to protect the chip in case of an over-voltage condition. Capacitor C13 filters high frequency ripples on the chip supply voltage (Vcc).

Soft-Start

A soft-start function is activated during start-up, and can be adjusted by capacitor C14. In addition to start-up, soft-start is activated at each restart attempt during auto-restart and when restarting after one of the several protection functions are activated. This effectively minimizes current and voltage stresses on the CoolMOS MOSFET, the snubber network, and the output rectifier during start-up. The soft-start feature further helps to minimize output overshoot and prevents saturation of the transformer during start-up.

Clamping network

The clamping network which consists of a diode (D3), a resistor (R10) and a capacitor (C12) clamps the voltage spike caused by the transformer leakage inductance to a safe value this limits the avalanche losses of the CoolMOS transistor.



Control Loop

The resistors R1 and R2 represent the voltage divider for the reference diode TL431CLP (IC2). R4 supplies the TL431CLP reference diode with a minimum current and R3 the LED of the optocoupler. The network which consists of capacitors C1 and C2 determines the corner frequencies fg1 and fg2. R5 sets the gain of the control loop.

Slope Compensation

The current mode controller becomes unstable whenever the steady – state duty cycle D is larger than 0.5. In order to realize a design with a duty cycle greater 0.5, the slope of the current needs to be compensated. The slope compensation is realized by the network consisting of capacitor C17, C18 and the resistor R19.

Ripple Reduction

Inductor L5 and capacitor C23 attenuate the differential – mode emission currents caused by the fundamental and harmonic frequencies of the primary current waveform.

SMPS Calculation Software FLYCAL

FLYCAL is an EXCEL spread sheet with all Equations needed for the easy calculaton of your SMPS. FLYCAL corresponds with the calculaton example in this application note. You only have to enter the main parameters of your application in FLYCAL and to follow step by step the principle outlined in the calculation example. FLYCAL contains all equations used in the example with the same consecutive numbering.



Circuit Diagram:

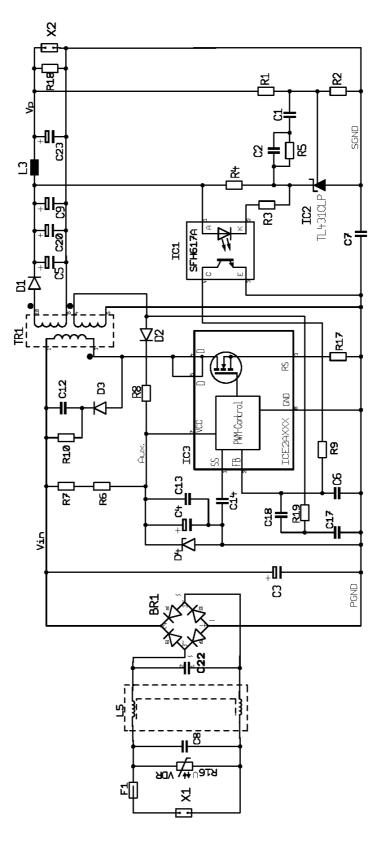


Fig. 3



Protection Functions

The block diagram displayed in Fig. 4 shows the interal functions of the protection unit. The comparators C1, C2, C3 and C4 compare the soft-start and feedback-pin voltages. Logic gates connected to the comparator outputs ensure the combination of the signals and enables the setting of the "Error-Latch".

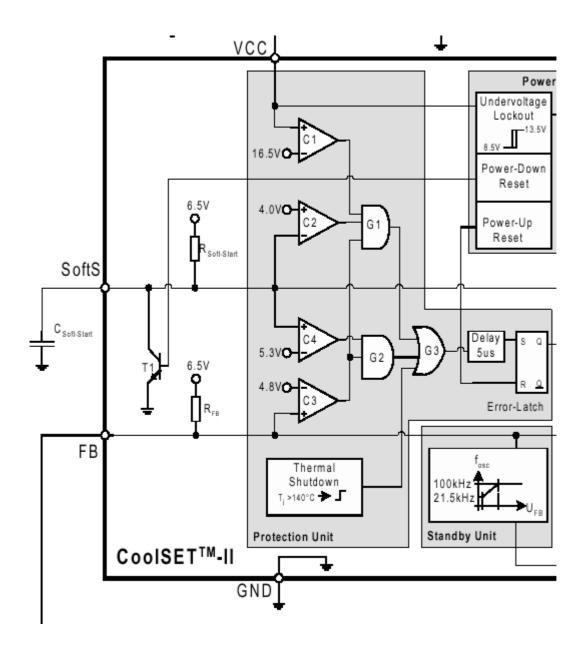






Fig. 5 shows the relation between the voltages at the soft start (Vss) and the feedback pins (V_{FB}) of **ICE2AXXX**, as a function of the supply voltage (Vcc) during an overvoltage condition at CoolSET soft start.

Depending on the voltage levels at the inputs, the overvoltage and (Vcc – PIN 7) and overload (V_{FB} – PIN 2) protection functions are activated.

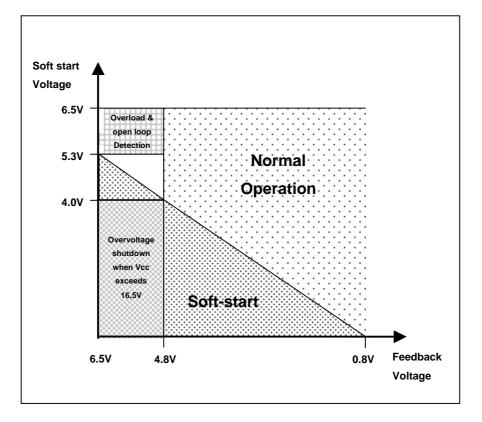
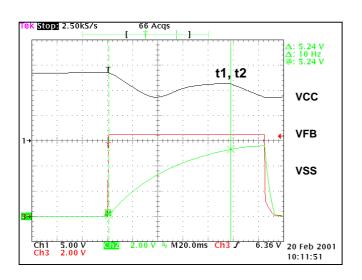


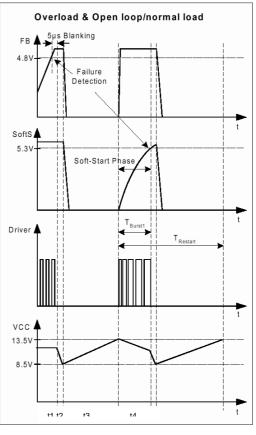
Fig. 5



Overload and Open-Loop Protection

- Feedback voltage (VFB) exceeds 4.8V and soft start voltage (VSS) is above 5.3V (soft start is completed) (t1)
- After a 5µs delay the **CoolMOS** is switched off (t2)
- Voltage at Vcc Pin (VCC) decreases to 8.5V (t2)
- Control logic is switched off (t3)
- Start-up resistor charges Vcc capacitor (t3)
- Operation starts again with soft start after Vcc voltage has exceeded 13.5V (t4)







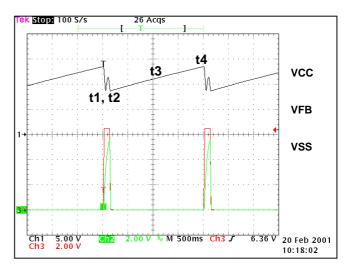


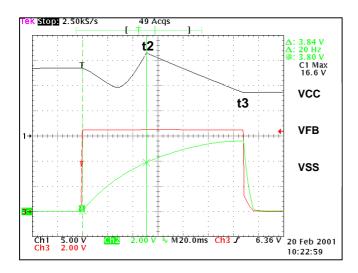
Fig. 8

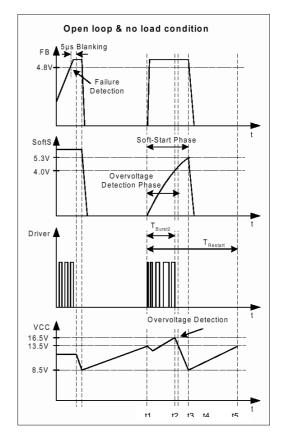
Fig. 7



Overvoltage Protection During Soft Start

- Feedback voltage (VFB) exceeds 4.8V and soft-start voltage (VSS) is below 4.0V (soft start phase) (t1)
- Voltage at Vcc pin (VCC) exceeds 16.5V (t2)
- CoolMOS transistor is immediately switched off (t2)
- Voltage at VCC pin decreases to 8.5V (t3)
- Control logic is switched off (t3)
- Start-up resistor charges VCC capacitor (t4)
- Operation starts again with soft start after VCC voltage has exceeded 13.5V (t5)









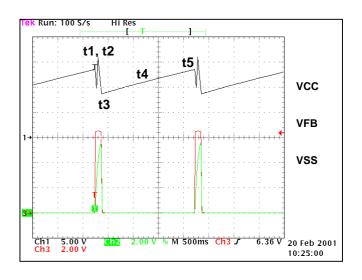


Fig. 11



Frequency Reduction

The frequency of the oscillator depends on the voltage at pin FB. Below a voltage of typ. 1.75V the frequency decreases down to 21.5 kHz. Due to this frequency reduction the power losses in low load condition can be reduced very effectively. This dependency is shown in Fig. 12

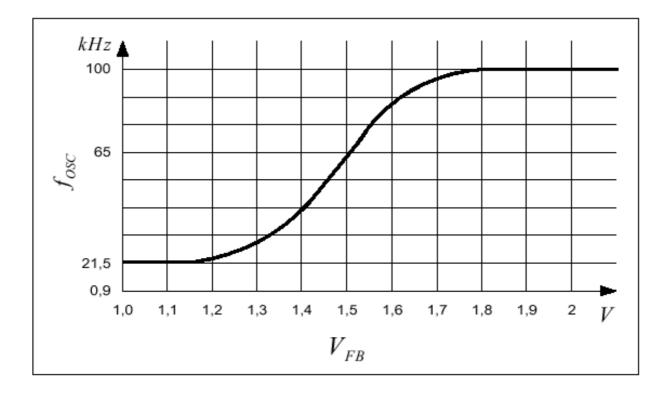


Fig. 12



Design Procedure

for fixed frequency Flyback Converter with ICE2AXXX operating in discontinuous current mode.

Procedu	re	Example	
Define input Parameters:			
Minimal AC input voltage:	V _{AC min}	90V	
Maximal AC input voltage:	V _{AC max}	264V	
Line frequency:	f _{AC}	50Hz	
Max. output power:	P _{OUT max}	50W	
Nom. output power:	P _{OUT nom}	40W	
Min. output power:	P _{OUT min}	0,5W	
Output voltage:	V _{OUT}	16V	
Output ripple voltage:	V _{OUT Ripple}	0,05V	
Reflection voltage:	V _{Rmax}	120V	
Estimated efficiency:	η	0,85	
DC ripple voltage:	V _{DC IN Ripple}	30V	
Auxiliary voltage:	V _{Aux}	12V	
Optocoupler gain:	G _c	1	
Used CoolSET		ICE2A365	
		I	
There are no special requirem	nents imposed on		
the input rectifier and storage	capacitor in the		
flyback converter. The compo	nents will be		
selected to meet the power ra	iting and hold-up		
requirements.			
Maximum input power:			
$P_{IN \max} = \frac{P_{OUT \max}}{n}$	(Eq 1)	50W 50W	
η	(=9)	$P_{IN \max} = \frac{50W}{0.85} = 59W$	
		1	



Input Diode Bridge (BR1):
$$I_{ACRMS} = \frac{P_{DVMX}}{V_{ACmin} \cdot \cos \varphi}$$
 (Eq 2) $I_{ACRMS} = \frac{59W}{90V \cdot 0.6} = 1.09A$ Maximum DC IN voltage
 $V_{DCmax PK} = V_{ACmin} \cdot \sqrt{2}$ (Eq 3) $V_{DC max PK} = 264V \cdot \sqrt{2} = 373V$ Determine Input Capacitor (C3):
Minimum peak input voltage at "no load" condition
 $V_{DC min PK} = V_{AC min} \cdot \sqrt{2}$ (Eq 4) $V_{DC min PK} = 90V \cdot \sqrt{2} = 127V$ We choose a ripple voltage of 30V
 $V_{DC min PK} = V_{DC min PK} - V_{Ripple}$ (Eq 5)we choose a ripple voltage of 30V
 $V_{DC min = 127V - 30V = 97V$ Calculation of discharging time at each half-line
cycle: $T_D = 5ms \cdot \left(1 + \frac{\arcsin \frac{V_{DC min PK}}{90}}{90} - (Eq 6)\right)$ $T_D = 5ms \cdot \left(1 + \frac{\arcsin \frac{97V}{127V}}{90} = 7.7ms$ Required energy at discharging time of C3:
 $W_{DV} = P_{N max} \cdot T_D$ (Eq 7) $W_{IN} = 59W \cdot 7.7ms = 0.46Ws$ Calculation of input capacitor value C_{IN} :
 $C_{IN} = \frac{2 \cdot W_{IN}}{V_{DC min FK} - V_{DC min}}$ (Eq 8) $C_{IN} = \frac{2 \cdot 0.46Ws}{16129V^2 - 9409V^2} = 136.9\mu F$



1

Alternatively a rule of thumb for choosing C_{IN} can be applied:	
Input voltage C _{IN} 115V 2μF/W 230V 1μF/W 85V270V 23μF/W	$59W \cdot 3\frac{\mu F}{W} = 177 \mu F$
Recalculation of input Capacitor:	
Select a capacitor from the Epcos Databook of Aluminium Electrolytic Capacitors .	
The following types are preferred :	
For 85°C Applications:Series B433032000h life timeB4350110000h life time	
For 105°C Applications:Series B435043000h life timeB435055000h life time	We choose 150μF 400V (based on Eq 8)
$V_{DC\min} = \sqrt{V_{DC\min PK}^2 - \frac{2 \cdot W_{IN}}{C_{IN}}} $ (Eq 9)	$V_{DC\min} = \sqrt{16129V^2 - \frac{2 \cdot 0.46Ws}{150\mu F}} = 100V$
Note that special requirements for hold up time, including cycle skip/dropout, or other factors which affect the resulting minimum DC input voltage and capacitor time should be considered at this point also.	



Transformer Design (TR1):

Calculation of peak current of primary inductance: $D_{\max} = \frac{V_{R\max}}{V_{R\max} + V_{DC\min}}$ (Eq 10a) $I_{LPK} = \frac{2 \cdot P_{IN MAX}}{V_{DC \min} \cdot D_{\max}}$ (Eq 10b) $I_{LRMS} = I_{LPK} \cdot \sqrt{\frac{D_{\text{max}}}{3}}$ (Eq 11) Calculation of primary inductance within the limit of maximum Duty-Cycle : $L_P = \frac{D_{\max} \cdot V_{DC\min}}{I_{LPK} \cdot f}$ (Eq 12) Selected core: E 25/13/7 Select core type and inductance factor (AL) from Epcos Material = N27 "Ferrite Databook" or CD-ROM A_L = 111 nH "Passive Components". s = 0,75 mm Fix maximum flux density: $A_e = 52 \text{ mm}^2$ $B_{max} \approx 0.2T \dots 0.3T$ for ferrite cores depending on core material. $A_{\rm N} = 61 \, {\rm mm}^2$ We choose 0,2T for material N27 $I_{N} = 57,5 \text{ mm}$ The number of primary turns can be calculated as: $N_P = \sqrt{\frac{L_P}{A_L}}$ (Eq 13) The number of secondary turns can be calculated as: $Ns = \frac{N_P \cdot \left(V_{OUT} + V_{FDIODE}\right)}{V_{R \max}}$ (Eq 14)

The number of auxiliary turns can be calculated as:

$$N_{Aux} = \frac{Ns \cdot (V_{Aux} + V_{FDIODE})}{V_{R \max}}$$
(Eq 15)

$$D_{\max} = \frac{120V}{120V + 100V} = 0,55$$

$$I_{LPK} = \frac{2 \cdot 59W}{100V \cdot 0.55} = 2,16A$$

$$I_{LRMS} = 2,16A \cdot \sqrt{\frac{0,55}{3}} = 0,92A$$

$$L_P = \frac{0,55 \cdot 100V}{2,16A \cdot 100 * 10^3 Hz} = 253 \mu H$$

$$N_P = \sqrt{\frac{253\mu H}{111nH}} = 47,7$$
 turns

we choose Np = 46 turns

$$Ns = \frac{46 \cdot (16V + 0.8V)}{120V} = 6.46$$

$$Ns = \frac{46 \cdot (12V + 0.7V)}{120V} = 5.6$$

we choose N_{Aux} = 5 turns

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Verification of primary inductance, primary peak current, max. duty cycle, flux density and gap: (Eq 16) $L_P = 46^2 \cdot 111 nH = 235 \mu H$ $L_{P} = N_{P}^{2} \cdot A_{I}$ (Eq 17) $I_{LPK} = \sqrt{\frac{59W}{0.5 \cdot 235 \mu H \cdot 100 * 10^3 Hz}} = 2.24 A$ $I_{LPK} = \sqrt{\frac{P_{IN \max}}{0.5 \cdot Lp \cdot f}}$ $V_R = \frac{(V_{OUT} + V_{FDIODE}) \cdot N_P}{N_S}$ (Eq 18) $V_R = \frac{(16V + 0.8V) \cdot 46}{7} = 110V$ (Eq 19) $D_{\text{max}} = \frac{235\mu H \cdot 2,24A \cdot 100kHz}{100V} = 0,53$ $D_{\max} = \frac{L_P \cdot I_{LPK} \cdot f}{V_{DC\min}}$ (Eq 20) $D'_{\text{max}} = \frac{235\mu H \cdot 2,24A \cdot 100kHz}{110V} = 0,47$ $D'_{\max} = \frac{L_P \cdot I_{LPK} \cdot f}{V_P}$ (Eq 21) $B_{\text{max}} = \frac{235\mu H \cdot 2,24A}{46 \cdot 52mm^2} = 210mT$ $B_{\max} = \frac{L_P \cdot I_{LPK}}{N_P \cdot A}$ (Eq 22) $s = \frac{4 \cdot \pi \cdot 10^{-7} \cdot 46^2 \cdot 52mm^2}{235\mu H} = 0,588mm$ $s = \frac{4 \cdot \pi \cdot 10^{-7} \cdot N_P^2 \cdot A_e}{L_P}$ Sense resistor The sense resistance R_{Sense} can be used to individually define the maximum peak current and thus the maximum power transmitted. Caution: When calculating the maximum peak current, short term peaks in output-power must also be Vcsth = 1.0V typ. (taken from data sheet) taken into consideration. $R_{Sense} = \frac{V_{csth}}{I_{IPK}}$ (Eq23) $R_{Sense} = \frac{1,0V}{2.24A} = 0,45\Omega$ we select $0,43\Omega$ $I_{I PK} = 2,33A$ POUTmax = 54W



Winding Design:	
see also page 38	
Transformer Construction	
The primary winding of 46 turns has to be divide	t l
into 23+23 turns in order to get the best coupling	
between primary and secondary winding.	
	From bobbin datasheet E25/13/7: BW = 15,6mm
The effective bobbin width and winding cross	Margin determined: $M = 0$ mm
section can be calculated as:	we use triple insulated wire for secondary
	winding
	DW/ 15.6
$BW_e = BW - 2 \cdot M \tag{Eq 24}$	$BW_e = 15,6mm$
$A_{Ne} = \frac{A_N \cdot BW_e}{BW} $ (Eq 25)	$A_{Ne} = 61mm^2$
BW	
Calculate copper section for primary and	
secondary winding:	
The winding cross section A_{N} has to be	
subdivided according to the number of windings.	
Primary winding 0,5	
Secondary winding 0,45	
Auxiliary winding 0,05	
Copper space factor f_{Cu} :0,20,4	We calculate the available area for each winding:
., ,	Used for calculation: $f_{Cu} = 0,3$
$0.5 \cdot A_{yy} \cdot f_{xy} \cdot BW$	
$A_P = \frac{0.5 \cdot A_N \cdot f_{Cu} \cdot BW_e}{N_P \cdot BW} $ (Eq 26)	$A_P = \frac{0.5 \cdot 61mm^2 \cdot 0.3}{46} = 0.2mm^2$
$-r_{F} = \cdots$	46
$AWG = 9.97 \cdot (1.8277 - (2 \cdot \log(d)))$ (Eq 27)	diameter dp \approx 0,5mm 25 AWG
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$$A_{n} = \frac{0.45 \cdot A_{W} \cdot f_{CS} \cdot BW_{n}}{N_{n} \cdot BW}$$
(Eq 28) $A_{n} = \frac{0.45 \cdot 6 \ln m^{2} \cdot 0.3}{7} = 1.18 mm^{2}$ $A_{aux} = \frac{0.05 \cdot A_{N} \cdot f_{Cu} \cdot BW_{n}}{N_{aux} \cdot BW}$ (Eq 29) $A_{aux} = \frac{0.05 \cdot 6 \ln m^{2} \cdot 0.3}{5} = 0.18 mm^{2}$ With the effective bobbin width we check the number of turns per layer:Primary: $N_{r} = \frac{BW_{r}}{d_{p}}$ (Eq 30) $N_{r} = \frac{15.6 mm}{0.46 mm} = 31$ turns per layer 2 layer neededSecondary: $N_{s} = \frac{15.6 mm}{2 \cdot 1.21 mm} = 6$ turns per layer 2 layer neededAuxilliary:1 layer !



Output Rectifier (D1):

The output rectifier diodes in flyback converters are subjected to a large PEAK and RMS current stress. The values depend on the load and operating mode. The voltage requirements depend on the output voltage and the transformer winding ratio.

Calculation of the maximum reverse voltage:

$$V_{RDiode} = V_{OUT} + \left(V_{DC \max PK} \cdot \frac{N_s}{N_P}\right) \qquad \text{(Eq 31)} \qquad V_{RDiode} = 16V + \left(373V \cdot \frac{7}{46}\right) = 72,8V$$

Calculation of the maximum current on secondary side:

$$I_{SPK} = I_{LPK} \cdot \frac{N_P}{N_S}$$
(Eq 32)

$$I_{SRMS} = I_{SPK} \cdot \sqrt{\frac{1}{3} \cdot D'_{\text{max}}}$$
 (Eq 33)

$$I_{SPK} = 2,55A \cdot \sqrt{7}$$

$$I_{SRMS} = 15,3A \cdot \sqrt{\frac{1}{3} \cdot 0,47} = 5,9A$$

 $-2334.\frac{46}{-1534}$

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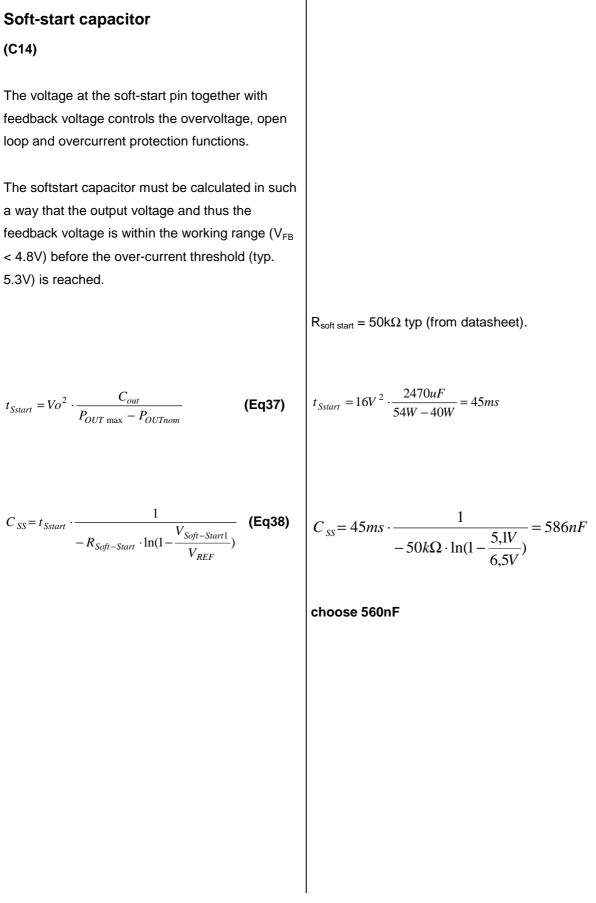


Output Capacitors (C5, C9):	To calculate the output capacitor, it is necessary to set the maximum voltage overshoot in case o switching off @ maximum load condition.		
Output capacitors are highly stressed in flyback	After switching off the load, the control loop		
converters. Normally the capacitor will be selected	needs about 1020 internal clock periods to		
for 3 major parameters: capacitance value, low	reduce the duty cycle.		
ESR and ripple current rating.			
Max. voltage overshoot: ΔV_{OUT}	$\Delta V_{OUT} = 0,5V$		
Number of clock periods: n _{CP}	$\Delta V_{OUT} = 0,5V$ $n_{CP} = 20$		
$C_{OUT} = \frac{I_{OUT \max} \cdot \mathbf{n}_{CP}}{\Delta V_{OUT} \cdot f}$ (Eq 34)	$C_{OUT} = \frac{3,1A \cdot 20}{0,5V \cdot 100 * 10^3 Hz} = 1250 \mu F$		
$I_{OUT} = \frac{P_{OUT \max}}{V_{OUT}}$ (Eq 34a)	$I_{OUT} = \frac{50W}{16V} = 3.1A$ $I_{Ripple} = \sqrt{5.9A^2 - 3.1A^2} = 5.0A$		
$I_{Ripple} = \sqrt{I_{SRMS}^2 - I_{OUT}^2} $ (Eq 34b)	$I_{Ripple} = \sqrt{5,9A^2 - 3,1A^2} = 5,0A$		
Select a capacitor out of Epcos Databook for Aluminium Electrolytic Capacitors .			
The following types are preferred :	We select 1000μF 35V (based on Eq 34):		
For 105°C Applications low impedance:	B41859-F7108-M		
Series B41856 4000h life time			
	ESR ≈ Zmax = 0,034Ω @ 100kHz		
For 105°C Applications lowest impedance:			
Series B41859 4000h life time	lac _R = 1,94A		
	we need 2 capacitors in parallel		

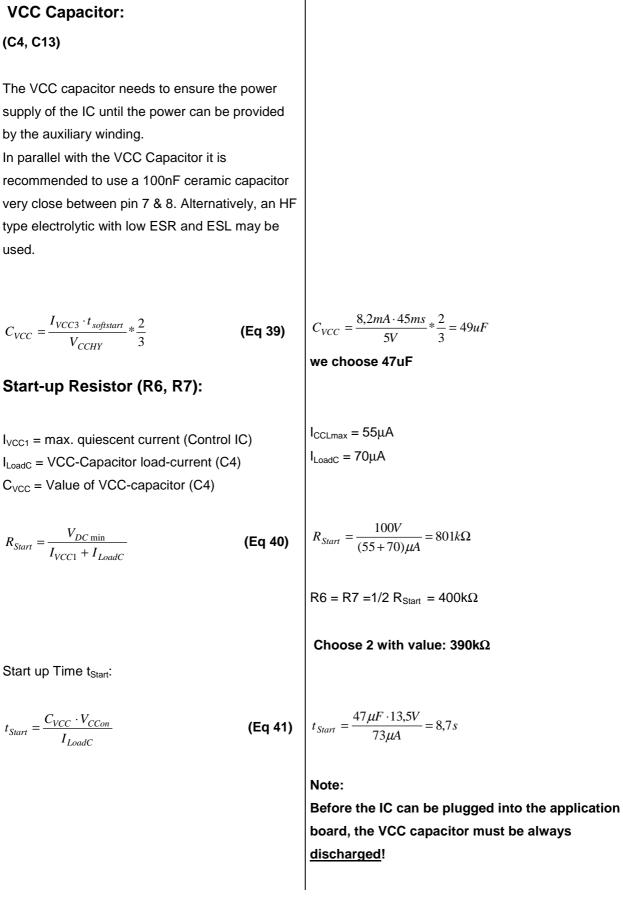


Output Filter (L3, C23): The output filter consists of one capacitor (C23) and one inductor (L3) in a L-C filter topology. Zero frequency of output capacitor (C5,C9, C20) and associated ESR: $f_{ZCOUT} = \frac{1}{2 \cdot \pi \cdot R_{ESR} \cdot C_{OUT}}$ (Eq 35) $f_{ZCOUT} = \frac{1}{2 \cdot \pi \cdot 0.034 \Omega \cdot 1000 \mu F} = 4.7 k Hz$ Calculation of the inductance (L3) needed for the We use C_{LC} (C23) 470uF substitution of the zero caused by the output capacitors: $L_{OUT} = \frac{(C_{OUT} \cdot R_{ESR})^2}{C_{IC}}$ (Eq 36) $L_{OUT} = \frac{(1000uF \cdot 0.034\Omega)^2}{470uF} = 2.5uH$ **RC-Filter at Feedback Pin** (C6, R9) The RC Filter at the Feedback pin is designed to supress any noise which may be coupled in on this track. Typical values: C6:1...4,7nF R9:22 Ohm Note that the value of C6 interacts with the internal pullup (3,7k typical) to create a filter.











Clamping Network:	
(R10/C12/D3)	
$V_{Clamp} = V_{(BR)DSS} - V_{DC\max} - V_R $ (Eq 42)	$V_{Clamp} = 650V - 373V - 110V = 166V$
For calculating the clamping network it is necessary to know the leakage inductance. The most common way is to have the value of the leakage inductance (L_{LK}) given in percentage of the primary inductance (Lp). If it is known that the transformer construction is very consistent, measuring the primary leakage inductance by shorting the secondary windings will give an exact number (assuming the availability of a good LCR analyser).	In our example we choose 5% of the primary inductance for leakage inductance.
$L_{LK} = Lp \cdot x\%$	$L_{LK} = 235\mu H \cdot 5\% = 11,8\mu H$
$C_{Clamp} = \frac{I_{LPK}^{2} \cdot L_{LK}}{(V_R + V_{Clamp}) \cdot V_{Clamp}} $ (Eq 43)	$C_{Clamp} = \frac{(2,24A)^2 \cdot 11,8\mu H}{(110V + 166V) \cdot 166V} = 1,2nF \approx$ we choose 1,5nF
$R_{Clamp} = \frac{(V_{Clamp} + V_R)^2 - V_R^2}{0.5 \cdot L_{LK} \cdot I_{LPK}^2 \cdot f}$ (Eq 44)	$R_{Clamp} = \frac{(166V + 110V)^2 - 110V^2}{0.5 \cdot 11.8 \mu H \cdot (2.24A)^2 \cdot 100 * 10^3 Hz} = 23.9 k\Omega$ we choose 22kΩ
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Calculation of Losses:	
Input diode bridge (BR1):	
$P_{DIN} = I_{ACRMS} \cdot V_F \cdot 2 $ (Eq 45)	$P_{DIN} = 1,1A \cdot 1V \cdot 2 = 2,2W$ Copper resistivity p_{100} @ 100°C = 0,0172Ωmm ² /m
$R_{PCu} = \frac{l_N \cdot N_P \cdot p_{100}}{A_P} $ (Eq 46)	$R_{PCu} = \frac{0,0644m \cdot 46 \cdot 17,2m\Omega mm^2 / m}{0,46mm^2} = 277,1m\Omega$ $R_{SCu} = \frac{0,0644m \cdot 7 \cdot 17,2m\Omega mm^2 / m}{2,10mm^2} = 6,6m\Omega$
$P_{PCu} = I_{LPK}^2 \cdot D_{MAX} \cdot \frac{1}{3} \cdot R_{PCu} $ (Eq 47)	$P_{PCu} = (2,33A)^2 \cdot 0.53 \cdot \frac{1}{3} \cdot 277, 1m\Omega = 225, 7mW$ $P_{SCu} = (15,3A)^2 \cdot 0.47 \cdot \frac{1}{3} \cdot 2.01m\Omega = 227, 4mW$ $P_{Cu} = 225, 7mW + 227, 4mW = 453, 1mW$
$P_{SCu} = I_{SPK}^2 \cdot D'_{MAX} \cdot \frac{1}{3} \cdot R_{SCu}$	$P_{SCu} = (15,3A)^2 \cdot 0,47 \cdot \frac{1}{3} \cdot 2,01m\Omega = 227,4mW$
	$P_{Cu} = 225,7mW + 227,4mW = 453,1mW$
Output rectifier diode (D1):	
$P_{DDIODE} = I_{SPK} \cdot \sqrt{\frac{D'_{\text{max}}}{3}} \cdot V_{FDIODE} $ (Eq 48)	$P_{DDIODE} = 15,3A \cdot \sqrt{\frac{0,47}{3}} \cdot 0,8V = 5W$



COOLMOS TRANSISTOR: ICE2A365 $C_{o(er)} = 30pF$ Calculated @ $V_{DCmin} = 100V$ $C_{O} \approx 80pF$ ($C_{O} = C_{O(er)} + C_{Extern}$) $R_{DSON} = 1,1\Omega$ (@ 125°C)	
Switching losses:	(see also ICE2AXXX Data Sheet)
$P_{SON} = \frac{1}{2} \cdot C_O \cdot V_{DC\min}^2 \cdot f $ (Eq 49)	$P_{SON} = \frac{1}{2} \cdot 80 pF \cdot 100V^2 \cdot 100 * 10^3 Hz = 40 mW$
Conduction losses:	
$P_D = \frac{1}{3} \cdot R_{DSON} \cdot I_{LPK}^2 \cdot D_{\max} $ (Eq 50)	$P_D = \frac{1}{3} \cdot 1\Omega \cdot (2,33A)^2 \cdot 0,53 = 0,95W$
Summary of Losses:	
$P_{Losses} = P_{SON} + P_D $ (Eq 51)	$P_{Losses} = 40mW + 950mW = 0,99W$
Thermal Calculation:Table of typical thermal Resistance $[\frac{K}{W}]$:HeatsinkDIP8DIP7TO220No9096743 cm²64726 cm²5665	
$dT = P_{Losses} * R_{th} $ (Eq 52)	$dT = 0,99W * 56 \frac{K}{W} = 55,4K$
Tj = dT + Ta (Eq 53)	$Tj = 55,4K + 50^{\circ}C = 115,4^{\circ}C$



Fig. 13

Fig. 14

6,5

FΒ

R4 R1

∎ C1

C2

R2

R5

Vout

3,7

 V_{FB}

\$\$

R3

41

TL431

Regulation Loop:

Reference: TL431 (IC2) $V_{REF} = 2,5V$ $I_{KAmin} = 1mA$ Optocoupler: SFH617-3 (IC1) $Gc = 1 \dots 2 \equiv CTR \ 100\% \dots 200\%$ $V_{FD} = 1,2V$ $I_{Fmax} = 20mA$ (maximum current limit)

Primary side:

Feedback voltage: Values from ICE2AXXX datasheet $V_{Ref int} = 6,5V$ typ. $V_{FBmax} = 4,5V$ Av = 3,65 $R_{FB} = 3,7k$ typ.

$$I_{FB\max} = \frac{V_{\text{Re } f \text{ int}}}{R_{FB}}$$
(Eq 54)

$$I_{FB\min} = \frac{V_{\text{Refint}} - V_{FB\max}}{R_{FB}}$$
(Eq 55)

$$I_{FB\max} = \frac{6.5V}{3.7k\Omega} = 1.76mA$$

$$I_{FB\min} = \frac{6.5V - 4.6V}{3.7k\Omega} = 0.5mA$$

(Eq 56)
$$R_1 = 4,3k \cdot \left(\frac{16V}{2,5V} - 1\right) = 23,22k$$

the value of R2 can be fixed at 4,3k

Secondary side:

 $R_1 = R_2 \left(\frac{V_{OUT}}{V_{REF}} - 1 \right)$

$$R_3 \ge \frac{(V_{OUT} - (V_{FD} + V_{REF}))}{I_{F \max}}$$
 (Eq 57)

$$R_4 \leq \frac{V_{FD} + \left(R_3 \cdot \frac{I_{FB\min}}{Gc}\right)}{I_{KA\min}}$$

$$R_3 \ge \frac{(16V - (1, 2V + 2, 5V))}{20mA} = 0,74k \approx 0,75k$$

(Eq 58)
$$R_4 \leq \frac{1,2V + 0,75k \cdot \left(\frac{0,5mA}{1}\right)}{1mA} = 1,58k \approx 1,5k$$

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Regulation Loop Elements:

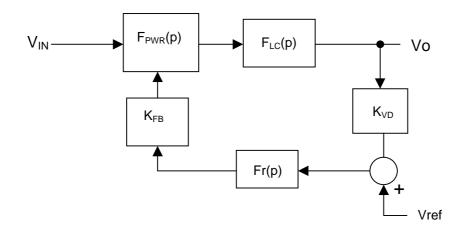


Fig. 15

Transfer Characteristics of Regulation Loop Elements:

$$K_{FB} = \frac{G_C \cdot 3k7}{R3}$$
 (Eq 59) Feedback

$$K_{VD} = \frac{R2}{R1 + R2} = \frac{V_{REF}}{V_{OUT}}$$
 (Eq 60) VoltageDivider

$$F_{PWR}(p) = \frac{1}{Z_{PWM}} \cdot \sqrt{\frac{R_L \cdot L_P \cdot f \cdot \eta}{2}} \cdot \left(\frac{\left(1 + p \cdot R_{ESR} \cdot C_5\right)}{\left(1 + p \cdot \left(\frac{R_L}{2} + R_{ESR}\right) \cdot C_5\right)} \right)$$
(Eq 61) Powerstage

 $Z_{\text{PWM}} = Transimpedance \ \Delta V_{\text{FB}} / \Delta I_{\text{D}}$

$$F_{LC}(p) = \frac{1 + p \cdot R_{ESR} \cdot C_9}{1 + p \cdot R_{ESR} \cdot C_9 + p^2 \cdot L \cdot C_9}$$
 (Eq 62) Output filter

$$Fr(p) = \frac{1 + p \cdot R5 \cdot (C1 + C2)}{p \cdot \frac{R1 \cdot R2}{R1 + R2} \cdot C1 \cdot (1 + p \cdot R5 \cdot C2)}$$
 (Eq 63) Regulator



Zeros and Poles of transfer characteristics:

Poles of powerstage @ min. and max. load:

$$R_{LH} = \frac{V_{OUT}^{2}}{P_{OUT \max}} = \frac{16V^{2}}{54W} = 4,9\Omega \quad \text{(Eq 64)} \qquad R_{LL} = \frac{V_{OUT}^{2}}{P_{OUT \min}} = \frac{16V^{2}}{0,5W} = 512\Omega \quad \text{(Eq 65)}$$

$$f_{OH} = \frac{1}{\pi \cdot R_{LH} \cdot C5} \qquad \qquad f_{OH} = \frac{1}{\pi \cdot 4,9\Omega \cdot 2000\mu F} = 31,1Hz \qquad (Eq 66)$$

$$f_{OL} = \frac{1}{\pi \cdot R_{LL} \cdot C5} \qquad \qquad f_{OL} = \frac{1}{\pi \cdot 512\Omega \cdot 2000\mu F} = 0.31 Hz$$
 (Eq 67)

We use the gain (Gc) of the optocoupler stage K_{FB} and the voltage divider K_{VD} as a constant.

$$K_{FB} = \frac{G_C \cdot 3k7}{R3}$$
 K_{FB} = 4,9 G_{FB} = 13,9db

$$K_{VD} = \frac{R2}{R1 + R2} = \frac{V_{REF}}{V_{OUT}}$$
 $K_{VD} = 0,15$ $G_{VD} = -16,4db$

With adjustment of the transfer characteristics of the regulator we want to reach equal gain within the operating range and to compensate the pole **fo** of the powerstage $F_{PWR}(\omega)$.

Because of the compensation of the output capacitor's zero (see page 22 Eq35, Eq36) we neglect it as well as the LC-Filter pole.

Consequently the transfer characteristic of the power stage is reduced to a single-pole response.

In order to calculate the gain of the open loop we have to select the cross-over frequency.

We calculate the gain of the Power-Stage with max. output power at the selected cross-over frequency

fg = 3kHz:



Calculation of transient impedance Z_{PWM} of ICE2AXXX

The transient impedance defines the direct relationship between the level of the peak current and the feedback pin voltage. It is required for the calculation of the power stage amplification. PWM-Op gain -Av = 3,65 (according to datasheet)

$$Z_{PWM} = \frac{\Delta V_{FB}}{\Delta I_{pk}} = A_v \cdot \frac{R_{sense}}{V_{csth}}$$

$$Z_{PWM} = \frac{\Delta V_{FB}}{\Delta I_{pk}} = 3,65 \cdot \frac{0,43\Omega}{1,00V} = 1,57 \frac{V}{A}$$
(Eq 68)

Gain @ crossover frequency:

$$\left|F_{PWR}(fg)\right| = \frac{1}{Z_{PWM}} \cdot \sqrt{\frac{R_L \cdot L_p \cdot f \cdot \eta}{2}} \cdot \left(\frac{1}{\sqrt{1 + \left(\frac{fg}{fo}\right)^2}}\right)$$
(Eq 69)

$$\left|F_{PWR}(3kHz)\right| = \frac{1}{1.7} \cdot \sqrt{\frac{5.1R \cdot 235\mu H \cdot 100kHz \cdot 0.8}{2}} \cdot \left(\frac{1}{\sqrt{1 + \left(\frac{3000}{31.1}\right)^2}}\right) = 0.05$$

 $G_{PWR}(3kHz) = \textbf{-26,2db}$



Transfer characteristics:

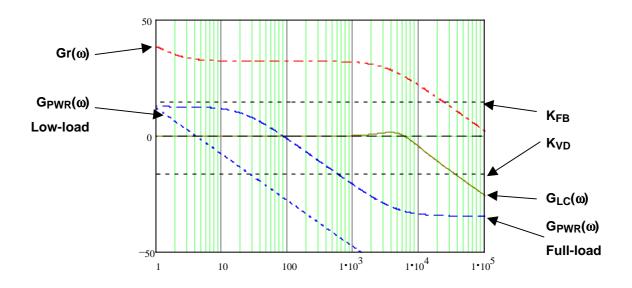


Fig. 16

At the crossover frequency (fg) we calculate the open loop gain:

$$G_{ol}(\omega) = Gs(\omega) + Gr(\omega) = 0.$$

With the equations for the transfer characteristics we calculate the gain of the regulation loop @ fg.

For the gain of the regulation loop we calculate:

 $Gs = G_{FB} + G_{PWR} + G_{VD} = 13,9db - 26,2db - 16,4db$

Gs = -28,7db

We calculate the separate components of the regulator:

Gs (ω) + Gr (ω) = 0 Gr = 0 - (-28,7db) = **28,7db**



$$Fr(p) = \frac{1 + p \cdot R5 \cdot (C1 + C2))}{p \cdot \frac{R1 \cdot R2}{R1 + R2} \cdot C1 \cdot (1 + p \cdot R5 \cdot C2)}$$

$$Gr = 20 \cdot \log \frac{R5 \cdot (R1 + R2)}{R1 \cdot R2} \qquad \qquad R5 = 10^{\frac{Gr}{20}} \cdot \frac{R1 \cdot R2}{R1 + R2}$$

$$R5 = 10^{\frac{32.2}{20}} \cdot 3,65k = 99,15k \approx 100k$$
 (Eq 70)

$$fp = \frac{1}{2 \cdot \pi \cdot R5 \cdot C2}$$

$$C2 = \frac{1}{2 \cdot \pi \cdot R5 \cdot fg}$$

$$C2 = \frac{1}{2 \cdot \pi \cdot 100k \cdot 3kHz} = 530 \, pF \approx 560 \text{pF} \quad \text{(Eq 71)}$$

In order to have enough phase margin @ low load condition we select the zero frequency of the compensation network to be at the middle between the min. and max. load poles of the power stage.

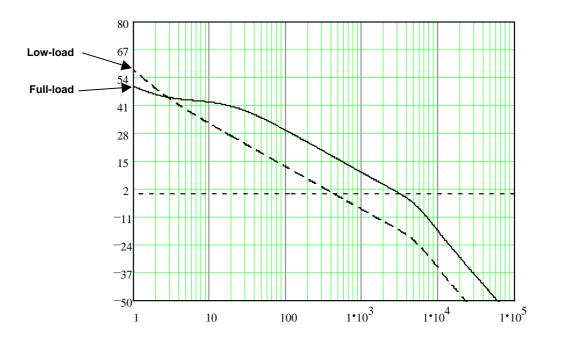
$$f_{om} = f_{oh} \cdot 10^{0.5 \cdot \log \frac{f_{ol}}{f_{oh}}} \qquad f_{om} = 31,1Hz \cdot 10^{0.5 \cdot \log \frac{0.15}{31,1}} = 3,2Hz$$

$$fz = \frac{1}{2 \cdot \pi \cdot R5 \cdot (C1 + C2)} \qquad C1 = \frac{1}{2 \cdot \pi \cdot R5 \cdot fom} - C2$$

$$C1 = \frac{1}{2 \cdot \pi \cdot 100k \cdot 3,2Hz} - 560\,pF = 492nF \approx 470nF \qquad (Eq 72)$$



Open Loop Gain





Open Loop Phase

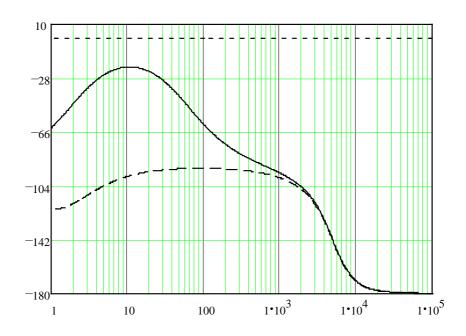
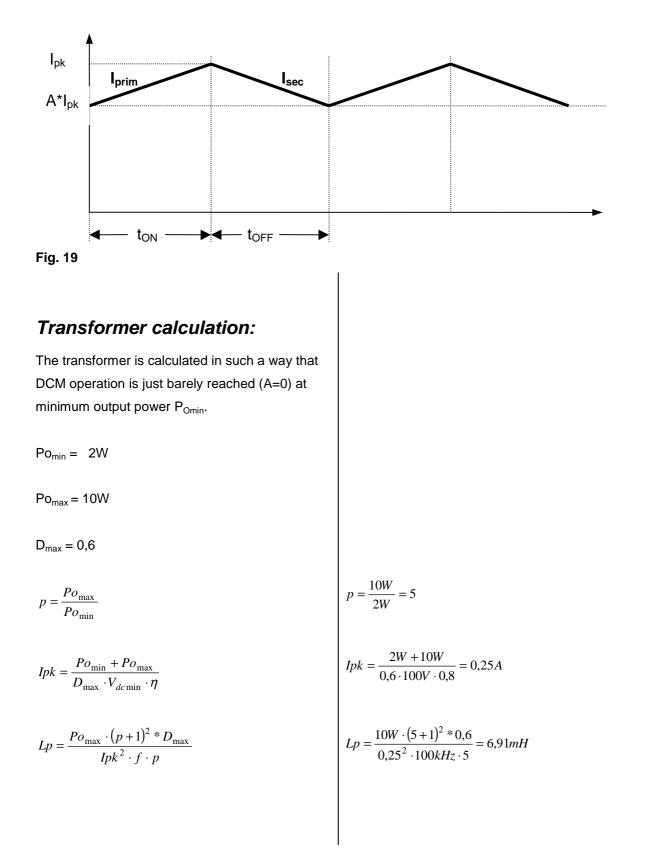


Fig. 18



Continuous Conduction Mode (CCM)





Slope Compensation

Slope compensation is necessary for stable regulator operation in **Continuous Conduction Mode (CCM)**, up to and beyond a duty cycle of 0.5 (see also [4]).

An simple method of slope compensation using the components R19, C17 and C18 is illustrated in the circuit diagram on page 3.

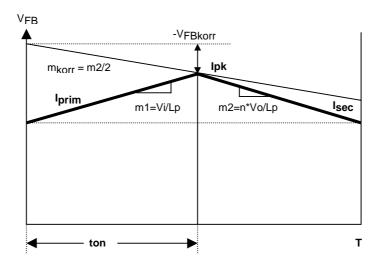


Fig. 20

 $V_R = n \cdot Vo$ n =

$$m2 = \frac{n \cdot Vo}{L_p} = \frac{V_R}{L_p} \qquad \qquad m_{korr} = \frac{m2}{2} = \frac{V_R}{2 \cdot L_p}$$

n.

For duty cycle = 0,5 applies:

$$m_{korr} = \frac{V_{FBkorr}}{5us} \qquad \qquad V_{FBkorr} = \left(\frac{V_R \cdot 5us}{2 \cdot L_p}\right) \cdot Z_{PWM}$$

 C_{Comp} (C17) is selected at 10nF. C18 is selected at 100nF.

R_{Comp} (R19):

$$R_{Comp} = -\frac{t}{\ln\left(1 - \frac{V_{FBkorr}}{VCC}\right) \cdot C_{Comp}}$$



Transformer Construction

The winding topology has a considerable influence on the performance and reliability of the transformer. In order to reduce leakage inductance and proximity to acceptable limits, the use of a sandwich construction is recommended. In order to meet international safety requirements a transformer for Off - Line power supply must have adequate insulation between primary and secondary windings.

This can be achieved by using a margin-wound construction or by using triple insulated wire for the secondary winding. The creepage distance for the universal input voltage range is typically 8mm. This results in a minimum margin width (as a half of the creepage distance) of 4mm. Additionally the neccesary insulation between primary and secondary winding is provided using three layers of basic insulation tape.

Example of winding topology for margin wound transformers:

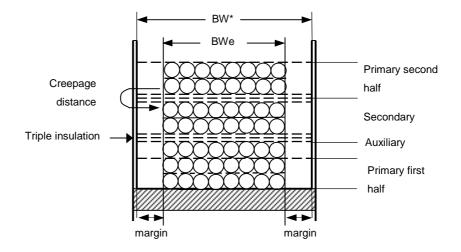


Fig. 21

Example of winding topology with triple insulated wire for secondary winding:

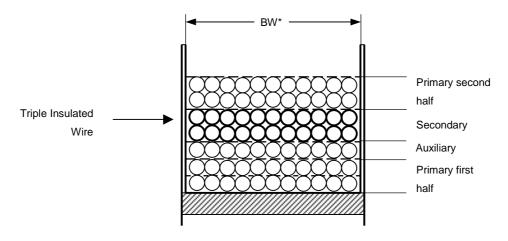


Fig. 22

BW* : value from bobbin datasheet



Layout Recommendation:

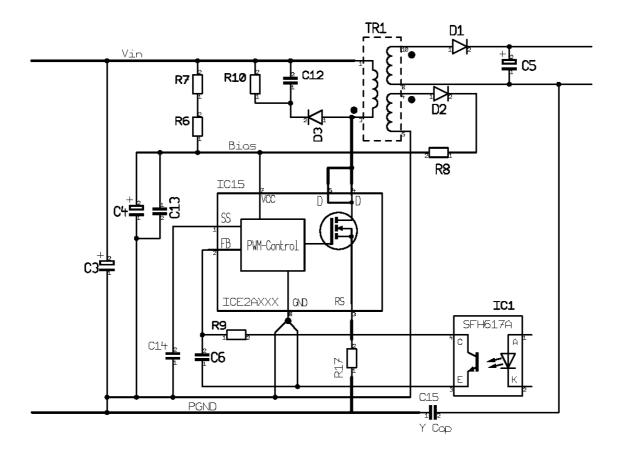


Fig. 23

In order to avoid crosstalk on the board between power and signal path we have to use care regarding the track layout when designing the PCB.

The power path (see Fig. 23) has to be as short as possible and needs to be separated from the VCC Path and the feedback path. All GND paths have to be connected together at pin 8 (star ground) of ICE2AXX.



CoolSET Table

DevICE	Package	Current	Rdson	Pout @	Pout @	Heatsink	Frequency
		Α	Ω	190Vacin	85Vacin		KHz
				Ta=75°C / Tj = 125°C	Ta=75°C / Tj = 125°C		
		•		V _{DS} =650V	•		•
ICE2A0565	DIP8	0.5	6.0	23	13	6 cm ²	100
ICE2A0565Z	DIP7	0.5	6.0	21	12	6 cm ²	100
ICE2A165	DIP8	1.0	3.0	31	18	6 cm ²	100
ICE2B165	DIP8	1.0	3.0	31	18	6 cm ²	67
ICE2A265	DIP8	2.0	0.9	52	32	6 cm ²	100
ICE2B265	DIP8	2.0	0.9	52	32	6 cm ²	67
ICE2A365	DIP8	3.0	0.45	67	45	6 cm ²	100
ICE2B365	DIP8	3.0	0.45	73	45	6 cm ²	67
ICE2A765P	TO220	7.0	0.5	240	130	2.7 k/W	100
ICE2B765P	TO220	7.0	0.5	240	130	2.7 k/W	67
V _{DS} =800V							
ICE2A180	DIP8	1.0	3.0	31	18	6 cm ²	100
ICE2A180Z	DIP7	1.0	3.0	29	17	6 cm ²	100
ICE2A280	DIP8	2.0	0.8	54	34	6 cm ²	100
ICE2A280Z	DIP7	2.0	0.8	50	31	6 cm ²	100

Output Power Notes:

The output power was created using the equations of this application note (see "Calculation of Losses" on page 27). It shows the maximum practical continuous power @ Ta = 75 °C and Tj = 125 °C with the recommended heatsink as a copper area on PCB for DIP7 / 8 and PDSO14 packages.



Summary of used Nomenclature

D	
B _{max}	Magnetic Inductance
BW	Bobbin Width
BWe	Effective Bobbin Width
CIN	Capacitance of Bulk Capacitor
COUT	Output Capacitance
Coss	Output Capacitance of CoolMOS
C _{Extern}	Output Capacitance of external Components
	Capacitance of Clamping – Capacitor
	Capacitance of VCC – Capacitor
D	Duty Cycle
D _{max}	Maximum Duty Cycle
f Dmax	Operating Frequency of CoolSET (f = 100kHz)
•	
f _{AC}	Line Frequency (Germany $F_{AC} = 50Hz$)
f _g ₄	Crossover Frequency
f _{Cu}	Copper Space Factor (0,2 0,4)
f _{OH}	Frequency Open Loop (High)
f _{Om}	Frequency Open Loop (middle)
f _{OL}	Frequency Open Loop (Low)
f _{ZCOUT}	Zero Frequency of output Capacitor
Gc	Optocoupler Gain
FBmax	Maximum Feedback Current
FBmin	Minimum Feedback Current
Fmax	Maximum Current (Optocoupler)
I _{KAmin}	Minimum Current (TL431)
LoadC	VCC – Capacitor Load – Current
I _{LPK}	Peak Current through the primary Inductance
ACRMS	Root Mean Square Current through the primary
Inductan	ce
I _{ACRMS}	Root Mean Square Current through the Bridge
Rectifier	
I _{PRI}	Primary Current @ time t
ISEC	Secondary Current @ time t
SPK	Peak Current through the secondary diode
I _{SPK} ISBMS	Peak Current through the secondary diode RMS Current through the secondary diode
I _{SRMS}	RMS Current through the secondary diode
I _{SRMS} I _{VCC1}	
I _{SRMS} I _{VCC1} IC)	RMS Current through the secondary diode Maximum quiescent Current of CoolSET (Control
I _{SRMS} I _{VCC1} IC) L _{OUT}	RMS Current through the secondary diode Maximum quiescent Current of CoolSET (Control Inductance output Filter
I _{SRMS} I _{VCC1} IC) L _{OUT} L _P	RMS Current through the secondary diode Maximum quiescent Current of CoolSET (Control Inductance output Filter Primary Inductance
I _{SRMS} Ivcc1 IC) L _{OUT} L _P L _{LK}	RMS Current through the secondary diode Maximum quiescent Current of CoolSET (Control Inductance output Filter Primary Inductance Leakage Inductance
I _{SRMS} IVCC1 IC) L _{OUT} L _P L _{LK} M	RMS Current through the secondary diode Maximum quiescent Current of CoolSET (Control Inductance output Filter Primary Inductance Leakage Inductance Margin (of Transformer)
I _{SRMS} IVCC1 IC) LOUT LP LLK M NCP	RMS Current through the secondary diode Maximum quiescent Current of CoolSET (Control Inductance output Filter Primary Inductance Leakage Inductance Margin (of Transformer) Number of Clock Periods
I _{SRMS} IVCC1 IC) LOUT L _P L _{LK} M n _{CP} n _p cout	RMS Current through the secondary diode Maximum quiescent Current of CoolSET (Control Inductance output Filter Primary Inductance Leakage Inductance Margin (of Transformer) Number of Clock Periods Number of parallel output Capacitors
Isrms Ivcc1 IC) Lout Lp Llk M ncp npcout Np	RMS Current through the secondary diode Maximum quiescent Current of CoolSET (Control Inductance output Filter Primary Inductance Leakage Inductance Margin (of Transformer) Number of Clock Periods Number of parallel output Capacitors Number of primary Turns
Isrms Ivcc1 IC) Lout Lp Llk M n _{CP} n _{pCOUT} Np Ns	RMS Current through the secondary diode Maximum quiescent Current of CoolSET (Control Inductance output Filter Primary Inductance Leakage Inductance Margin (of Transformer) Number of Clock Periods Number of parallel output Capacitors Number of primary Turns Number of secondary Turns
ISRMS IVCC1 IC) LOUT LP LLK M nCP npCOUT NP NS NAUX	RMS Current through the secondary diode Maximum quiescent Current of CoolSET (Control Inductance output Filter Primary Inductance Leakage Inductance Margin (of Transformer) Number of Clock Periods Number of parallel output Capacitors Number of primary Turns Number of secondary Turns Number of auxiliary Turns
ISRMS IVCC1 IC) LOUT LP LLK M n _C P n _p COUT NP NS NAUX PCU	RMS Current through the secondary diode Maximum quiescent Current of CoolSET (Control Inductance output Filter Primary Inductance Leakage Inductance Margin (of Transformer) Number of Clock Periods Number of parallel output Capacitors Number of primary Turns Number of secondary Turns Number of auxiliary Turns Power losses of Copper Resistor
ISRMS IVCC1 IC) LOUT LP LLK M n _C P n _p COUT NP NS NAUX PCU PD	RMS Current through the secondary diode Maximum quiescent Current of CoolSET (Control Inductance output Filter Primary Inductance Leakage Inductance Margin (of Transformer) Number of Clock Periods Number of parallel output Capacitors Number of primary Turns Number of secondary Turns Number of auxiliary Turns Power losses of Copper Resistor Conduction losses
ISRMS IVCC1 IC) LOUT LP LLK M n _{CP} n _{pCOUT} N _P Ns N _{AUX} P _{CU} P _D P _{DIN}	RMS Current through the secondary diode Maximum quiescent Current of CoolSET (Control Inductance output Filter Primary Inductance Leakage Inductance Margin (of Transformer) Number of Clock Periods Number of clock Periods Number of parallel output Capacitors Number of primary Turns Number of secondary Turns Number of auxiliary Turns Power losses of Copper Resistor Conduction losses Power losses input Diode
ISRMS IVCC1 IC) LOUT LP LLK M n _C P n _P COUT NP NS NAUX PCU PD ND PDIN PDDIODE	RMS Current through the secondary diode Maximum quiescent Current of CoolSET (Control Inductance output Filter Primary Inductance Leakage Inductance Margin (of Transformer) Number of Clock Periods Number of parallel output Capacitors Number of parallel output Capacitors Number of primary Turns Number of secondary Turns Number of auxiliary Turns Power losses of Copper Resistor Conduction losses Power losses input Diode Power losses rectifier Diode (secondary side)
ISRMS IVCC1 IC) LOUT LP LLK M nCP npCOUT NP NS NAUX PCU PD NS PCU PDIN PDIODE PIN MAX	RMS Current through the secondary diode Maximum quiescent Current of CoolSET (Control Inductance output Filter Primary Inductance Leakage Inductance Margin (of Transformer) Number of Clock Periods Number of parallel output Capacitors Number of parallel output Capacitors Number of secondary Turns Number of secondary Turns Number of auxiliary Turns Power losses of Copper Resistor Conduction losses Power losses input Diode Power losses rectifier Diode (secondary side) Maximum Input Power
ISRMS IVCC1 IC) LOUT LP LLK M n _C P n _P COUT NP NS NAUX PCU PD ND PDIN PDDIODE	RMS Current through the secondary diode Maximum quiescent Current of CoolSET (Control Inductance output Filter Primary Inductance Leakage Inductance Margin (of Transformer) Number of Clock Periods Number of parallel output Capacitors Number of primary Turns Number of secondary Turns Number of auxiliary Turns Power losses of Copper Resistor Conduction losses Power losses input Diode Power losses rectifier Diode (secondary side) Maximum Input Power Maximum Output Power
ISRMS IVCC1 IC) LOUT LP LLK M nCP npCOUT NP NS NAUX PCU PD NS PCU PDIN PDIODE PIN MAX	RMS Current through the secondary diode Maximum quiescent Current of CoolSET (Control Inductance output Filter Primary Inductance Leakage Inductance Margin (of Transformer) Number of Clock Periods Number of parallel output Capacitors Number of primary Turns Number of secondary Turns Number of secondary Turns Number of auxiliary Turns Power losses of Copper Resistor Conduction losses Power losses input Diode Power losses rectifier Diode (secondary side) Maximum Input Power Maximum Output Power
ISRMS IVCC1 IC) LOUT LP LLK M nCP NP NS NAUX PCU PD NS PDIN PDIODE PIN MAX POUT max POUT max POUT max	RMS Current through the secondary diode Maximum quiescent Current of CoolSET (Control Inductance output Filter Primary Inductance Leakage Inductance Margin (of Transformer) Number of Clock Periods Number of parallel output Capacitors Number of primary Turns Number of secondary Turns Number of secondary Turns Number of auxiliary Turns Power losses of Copper Resistor Conduction losses Power losses rectifier Diode Power losses rectifier Diode (secondary side) Maximum Input Power Maximum Output Power Minimum Output Power Power losses of Copper Resistor (primary
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Switching losses of CoolMOS Transistor (Off -PSOFE Operation)

Switching losses of CoolMOS Transistor (On -PSON

Operation) Copper Resistor (Transformer) R_{Cu} Resistance of switching CoolMOS Transistor (On R_{DSON} - Operation) RL Load - Resistance Maximum Load R_{LH} Minimum Load (defined by Designer) R_{LL} Internal Feedback Resistor (CoolSET) R_{FB} Copper Resistor of primary Inductance R_{PCu} Copper Resistor of secondary Inductance $\mathsf{R}_{\mathsf{SCu}}$ Clamping Resistor Start up Resistor R_{Clamp} $\mathsf{R}_{\mathsf{Start}}$ Time of one Period т Discharging Time of Input Capacitor C3 T_D On Time (CoolMOS) \mathbf{t}_{ON} Off Time (CoolMOS) t_{OFF} Rising Time (Voltage) tr Start up Time tStart Minimal AC Input Voltage $V_{AC min}$ $V_{AC\,\text{max}}$ Maximal AC Input Voltage V_{Aux} Auxiliary Voltage Drain Source Breakdown Voltage V_{(BR)DSS} Turn On Threshold for CoolSET @ Vcc - Pin V_{CCon} V_{DC IN} DC Input Voltage V_{DC IN max} Maximum DC Input Voltage V_{DC IN min} Minimum DC Input Voltage V_{DC max PK} Maximum DC Input Voltage Peak V_{DC min PK} Minimum DC Input Voltage Peak Minimum DC Input Voltage @ maximum load $V_{\text{DC min}}$ Reverse Voltage rectifier Diode (secondary side) V_{DDIODE} Maximum Feedback Voltage (CoolSET) V_{FBmax} Output Diode Forward Voltage V_{FDIODE} Forward Diode Voltage (Optocoupler) V_{FD} Vout Output Voltage (secondary Side) Output Ripple Voltage (secondary Side) V_{OUT Ripple} Reflected Voltage (from secondary side to primary V_R side) V_{RDiode} Reverse Voltage Diode Internal Reference Voltage (CoolSET) V_{Refint} Reference Voltage TL431 V_{REF} V_{Ripple} DC Ripple Voltage (on primary Side) Voltage on Sekondary Inductor VSEC $\mathsf{V}_{\mathsf{Clamp}}$ Maximum Voltage overshoot @ clamping network Discharging Energie Input Capacitor WIN Transimpedanz Z_{PWM}



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Page of	Page of	Subjects changed since last release		
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44		Second Issue		
40		CoolSET Table Update		

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